NSN 5962-01-333-0235

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View Online at https://aerobasegroup.com/nsn/5962-01-333-0235

Overall Height:

0.425 inches

Body Length:

1.290 inches

Body Width:

Between 0.500 inches and 0.610 inches

Body Height:

Between 0.150 inches and 0.210 inches

Maximum Power Dissipation Rating:

1.02 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Bipolar and programmable and schottky and w/active pull-up and high impedance and 3-state output

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

13 input

Criticality Code Justification:

Feat

Case Outline Source And Designator:

D-3 mil-m-38510

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 7.0 volts power source

Time Rating Per Chacteristic:

90.00 nanoseconds propagation delay time, low to high level output and 90.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Rom

Special Features:

Nuclear hardness critical item

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

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Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

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